SPICE Device Model SiRA90DP



Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

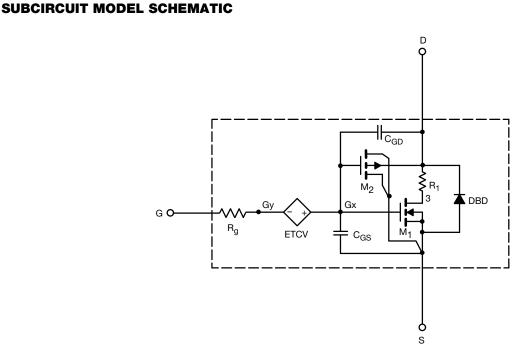
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over -55 °C to +125 °C temperature range
- Model the gate charge



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | |
|--|---------------------|--|-------------------|------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | SIMULATED DATA | MEASURED DATA | UNIT |
| Static | | | • | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS},I_{D}=250\;\mu A$ | 1.5 | - | V |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | 0.00064 | 0.00065 | Ω |
| | | $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 15 \text{ A}$ | 0.00093 | 0.00090 | |
| Forward Transconductance ^a | g fs | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | 64 | 110 | S |
| Body Diode Voltage | V _{SD} | I _S = 10 A | 0.66 | 0.68 | V |
| Dynamic ^b | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz | 9150 | 10 180 | pF |
| Output Capacitance | C _{oss} | | 3260 | 3290 | |
| Reverse Transfer Capacitance | C _{rss} | | 211 | 306 | |
| Total Gate Charge | Qg | $V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | 115 | 102 | nC |
| | | V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 20 A | 55 | 48 | |
| Gate-Source Charge | Q _{gs} | | 22 | 22 | |
| Gate-Drain Charge | Q _{gd} | | 4.7 | 4.7 | |

Notes

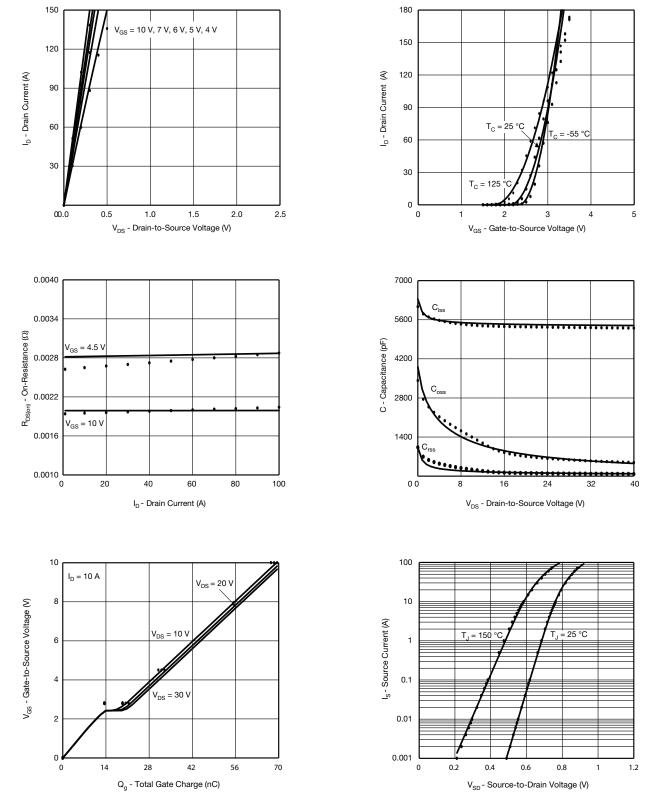
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.



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COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)



Note

• Dots and squares represent measured data. Copyright: Vishay Intertechnology, Inc.

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